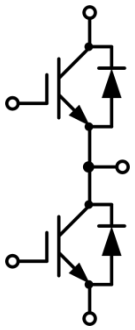
62mm Half Bridge IGBT Module

V_{CES}= 1700V, I_C= 200A, $V_{CE(sat)}$= 1.93V

Features

- 1700V Trench/Field Stop Technology
- Low switching losses
- Vcesat has a positive temperature coefficient



Applications

- Power Converters
- Uninterruptible power supplies
- Servo Drives
- Inverter

IGBT, Inverter

Maximum Ratings

Parameter	Symbol	Test Condition	Value	Unit
Collector-Emitter voltage	V_{CES}	T_{vj}=25℃	1700	V
Continuous DC collector current	$I_{C\ nom}$	T_C=100℃, $T_{vj\ max}$=175℃	200	A
Repetitive peak collector current	I_{CRM}	t_P=1ms	400	A
Total power dissipation	P_{tot}	T_C=25℃, $T_{vj\ max}$=175℃	1250	W
Gate-Emitter voltage	V_{GE}		±20	V

Characteristics Values

Parameter	Symbol	Test Condition		Value			Unit
				Min.	Typ.	Max.	
Collector-Emitter saturation voltage	V_{CEsat}	V_{GE}=15V, I_C=200A V_{GE}=15V, I_C=200A V_{GE}=15V, I_C=200A	T_{vj}=25℃ T_{vj}=125℃ T_{vj}=150℃		1.93 2.22 2.39	2.50	V
Gate-Emitter threshold voltage	$V_{GE(th)}$	I_C=8mA, V_{GE}=V_{CE}	T_{vj}=25℃	5.10	5.70	6.30	
Internal gate resistor	R_{Gint}				2.58		Ω
Gate charge	Q_G	V_{GE}=-15V…+15V			1.90		μC
Input capacitance	C_{ies}	f=1MHz, V_{CE}=25V, V_{GE}=0V	T_{vj}=25℃		27.18		nF
Reverse transfer capacitance	C_{res}				0.80		
Collector-emitter cut-off current	I_{CES}	V_{CE}=1700V , V_{GE}=0V	T_{vj}=25℃			2	mA
Gate-emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=20V	T_{vj}=25℃			200	nA
Turn-on delay time	$t_{d\ on}$	I_C=200A, V_{CE}=900V V_{GE}=±15V, R_G=3.3Ω (inductive load)	T_{vj}=25℃ T_{vj}=125℃ T_{vj}=150℃		194 212 224		ns

Rise time	t_r	I_C=200A, V_{CE}=900V, V_{GE}=±15V, R_G=3.3Ω, (inductive load)	T_{vj}=25℃ T_{vj}=125℃ T_{vj}=150℃		51 55 57	
Turn-off delay time	$t_{d\,off}$	I_C=200A, V_{CE}=900V, V_{GE}=±15V, R_G=3.3Ω, (inductive load)	T_{vj}=25℃ T_{vj}=125℃ T_{vj}=150℃		430 489 506	
Fall time	t_f	I_C=200A, V_{CE}=900V, V_{GE}=±15V, R_G=3.3Ω, (inductive load)	T_{vj}=25℃ T_{vj}=125℃ T_{vj}=150℃		303 352 368	
Turn-on energy loss per pulse	E_{on}	I_C=200A, V_{CE}=900V, V_{GE}=±15V, R_G=3.3Ω, (inductive load)	T_{vj}=25℃ T_{vj}=125℃ T_{vj}=150℃		31.88 40.73 43.77	mJ
Turn-off energy loss per pulse	E_{off}	I_C=200A, V_{CE}=900V, V_{GE}=±15V, R_G=3.3Ω, (inductive load)	T_{vj}=25℃ T_{vj}=125℃ T_{vj}=150℃		38.04 46.56 49.29	
SC data	I_{SC}	V_{GE}≤15V, V_{CC}=1000V, V_{CEmax}=V_{CES}-L_{sCE}·di/dt t_P≤10us, T_{vj}=150℃			1230	A
Thermal resistance, junction to case	R_{thJC}	per IGBT				0.12 K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150 ℃

Diode, Inverter

Maximum Ratings

Parameter	Symbol	Test Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	T_{vj}=25℃	1700	V
Continuous DC forward current	I_F		200	A
Repetitive peak forward current	I_{FRM}	t_p=1ms	400	A
I^2t-value	I^2t	t_p=10ms, sin180°, T_{vj}=125℃	10000	A^2s

Characteristics Values

Parameter	Symbol	Test Condition		Value			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F=200A, V_{GE}=0V I_F=200A, V_{GE}=0V I_F=200A, V_{GE}=0V	T_{vj}=25℃ T_{vj}=125℃ T_{vj}=150℃		2.07 2.28 2.24	2.50	V
Peak reverse recovery current	I_{RM}	I_F=200A -diF/dt=2430A/us(T_{vj}=150℃) V_R=900V, V_{GE}=-15V	T_{vj}=25℃ T_{vj}=125℃ T_{vj}=150℃		109 122 122		A
Recovered charge	Q_r	I_F=200A -diF/dt=2430A/us(T_{vj}=150℃) V_R=900V, V_{GE}=-15V	T_{vj}=25℃ T_{vj}=125℃ T_{vj}=150℃		22.80 38.70 39.90		μC
Reverse recovered energy	E_{rec}	I_F=200A -diF/dt=2430A/us(T_{vj}=150℃) V_R=900V, V_{GE}=-15V	Tvj=25℃ T_{vj}=125℃ T_{vj}=150℃		12.70 23.07 23.26		mJ
Thermal resistance, junction to case	R_{thJC}	per diode				0.16	K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	℃

Characteristics Values(Module)

Parameter	Symbol	Test Condition	Value			Unit
Isolation test voltage	V_{ISOL}	RMS, f=50Hz, t=1min		4000		V
Internal isolation				Al_2O_3		
Storage temperature	T_{stg}		-40		125	℃
Mounting torque for module mounting	M		3.0		6.0	Nm
Weight	W			318		g

Typical Characteristics

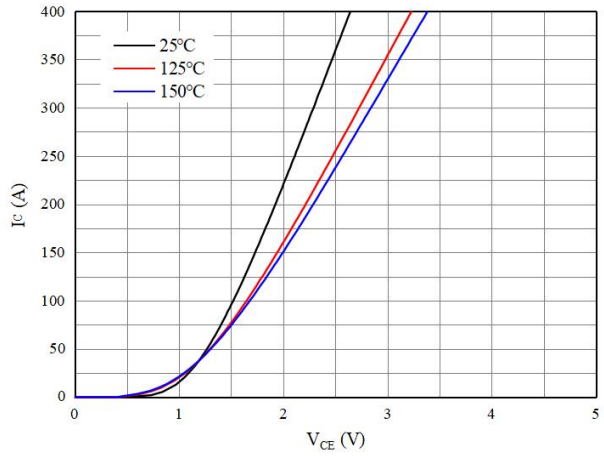


Fig 1. Typical output characteristics (V_{GE}=15V)

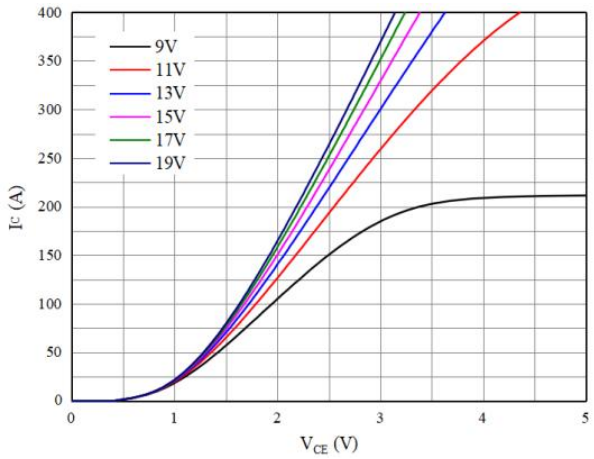


Fig 2. Typical output characteristics (T_{vj}=150℃)

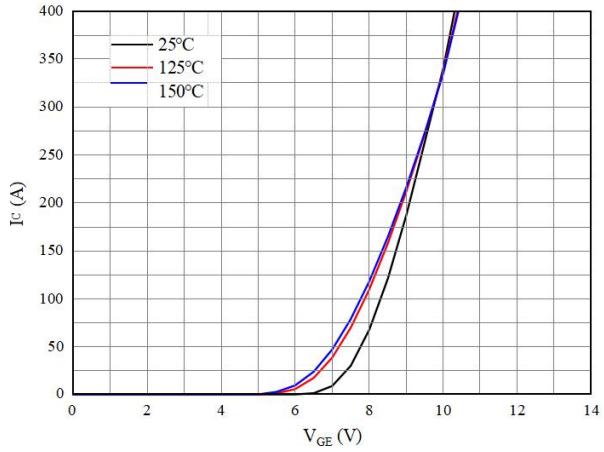


Fig 3. Typical transfer characteristic(V_{CE}=20V)

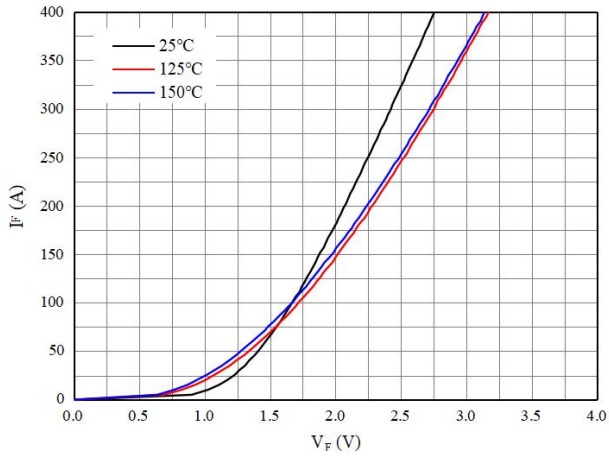


Fig 4. Forward characteristic of Diode

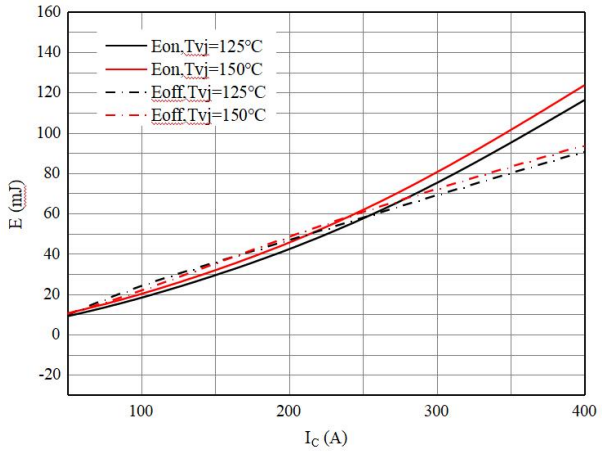


Fig 5. Switching losses of IGBT
V_{GE}=±15V, R_{Gon}=3.3Ω, R_{Goff}=3.3Ω, V_{CE}=900V

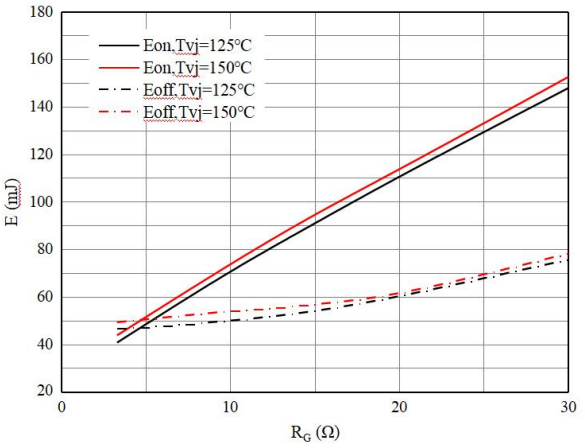


Fig 6. Switching losses of IGBT
V_{GE}=±15V, I_C=200A, V_{CE}=900V

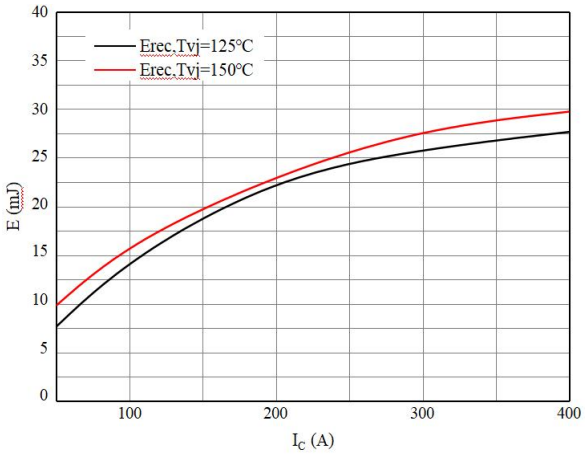


Fig 7. Switching losses of Diode
R_{Gon}=3.3Ω, V_{CE}=900V

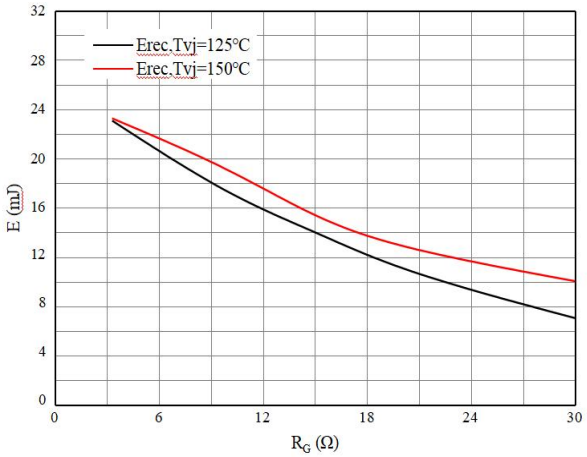


Fig 8. Switching losses of Diode
I_F=200A, V_{CE}=900V

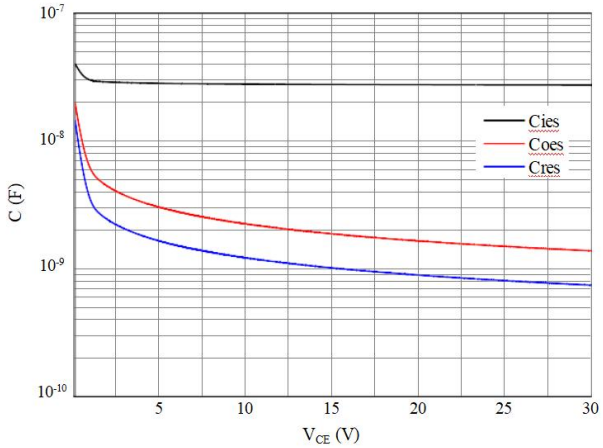
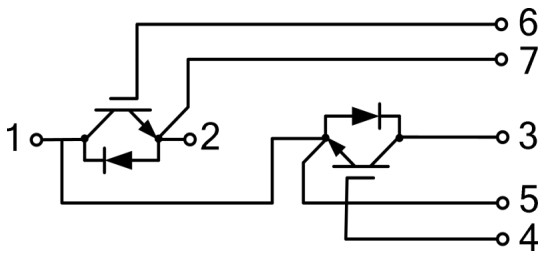
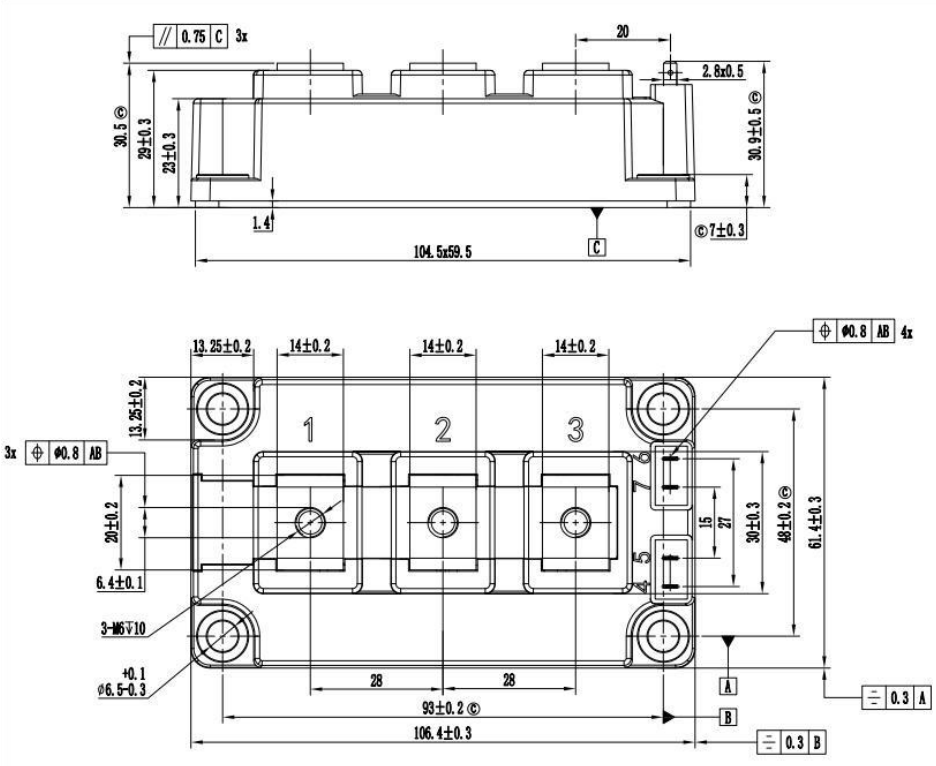


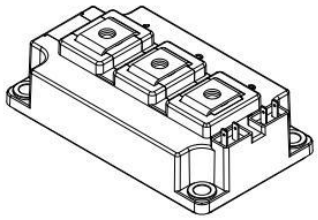
Fig 9. Capacitance characteristic

Circuit Diagram



Package Outlines(Unit: mm)





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